

TC74HCT563P TC74HCT573P

OCTAL D-TYPE LATCH WITH 3-STATE OUTPUT (TTL INPUT LEVEL)

TC74HCT563P INVERTING
TC74HCT573P NON-INVERTING

The TC74HCT563 and TC74HCT573 are high speed CMOS OCTAL LATCH with 3-STATE OUTPUT fabricated with silicon gate C²MOS technology.

These devices may be used as a level converter for interfacing TTL or NMOS to High Speed CMOS. The inputs are compatible with TTL, NMOS and CMOS output voltage levels.

They achieve the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

These 8-bit D-type latches are controlled by a latch enable input(LE) and a output enable input(\overline{OE}). While the LE input is held in high level, the Q outputs will follow the data input precisely or inversely. When the LE is take low, the Q outputs will be latched precisely or inversely at the logic level of D input data. While the \overline{OE} input is at low level, the eight outputs will be in a normal logic state (high or low logic level) and while high level the outputs will be in a high impedance state.

The application designer has a choice of combination of inverting and non-inverting outputs. The three-state output configuration and the wide choice of outline will make the bus-organized system simple. All inputs are equipped with protection circuits against static discharge or transient excess voltage.

FEATURES:

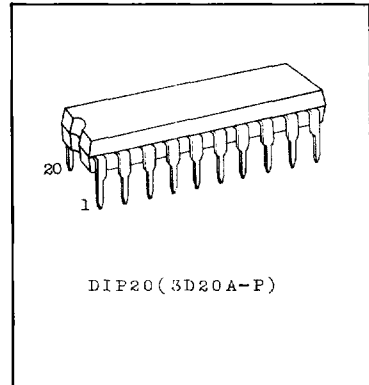
- High Speed $t_{pd}=20ns(Typ.)(V_{CC}=5V)$
- Low Power Dissipation $I_{CC}=4\mu A(Max.)(T_a=25^\circ C)$
- Compatible with TTL outputs $V_{IH}=2V(Min.)$,
 $V_{IL}=0.8V(Max.)$
- Output Drive Capability 15 LSTTL Loads
- Symmetrical Output Impedance $|I_{OH}|=I_{OL}=6mA$
- Pin and Function Compatible with 74LS563/573

TRUTH TABLE

INPUTS			OUTPUTS	
\overline{OE}	LE	D	Q (HCT573)	\overline{Q} (HCT563)
H	X	X	HZ	HZ
L	L	X	Q _n	\overline{Q}_n
L	H	L	L	H
L	H	H	H	L

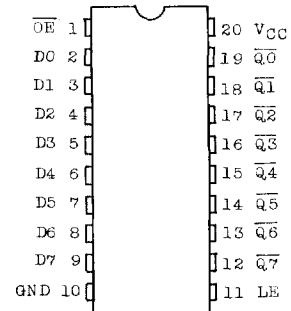
X : DON'T CARE
HZ : HIGH IMPEDANCE

Q_n : Q/ \overline{Q} OUTPUTS ARE LATCHED AT THE TIME WHEN THE LE INPUT IS TAKEN LOW LOGIC LEVEL.

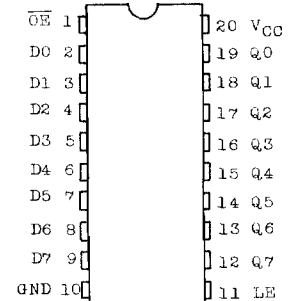


PIN ASSIGNMENT (TOP VIEW)

TC74HCT563

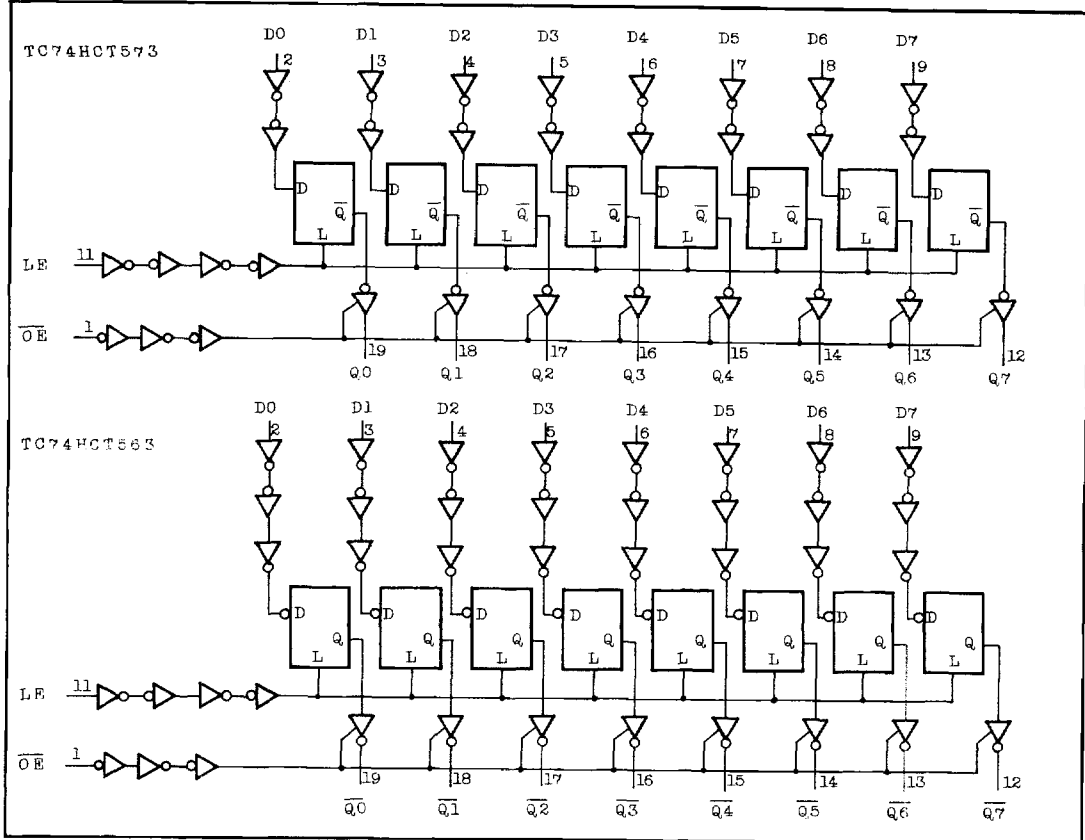


TC74HCT573



TC74HCT563P TC74HCT573P

LOGIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

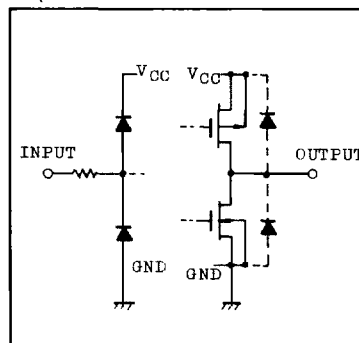
CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	V_{CC}	-0.5~7	V
DC Input Voltage	V_{IN}	-0.5~ $V_{CC}+0.5$	V
Bus Terminal Voltage	$V_{I/O}$	-0.5~ $V_{CC}+0.5$	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 20	mA
DC Output Current	I_{OUT}	± 35	mA
DC V_{CC} /Ground Current	I_{CC}	± 70	mA
Power Dissipation	P_D	500*	mW
Storage Temperature	T_{stg}	-65~150	$^{\circ}C$
Lead Temperature (10 sec)	T_L	300	$^{\circ}C$

* 500mW in the range of $T_a = -40^{\circ}C \sim 65^{\circ}C$ and from $T_a = 65^{\circ}C$ up to $85^{\circ}C$ derating factor of $-10mW/^{\circ}C$ shall be applied until 300mW.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	LIMIT	UNIT
Supply Voltage	V _{CC}	4.5 ~ 5.5	V
Input Voltage	V _{IN}	0 ~ V _{CC}	V
Output Voltage	V _{OUT}	0 ~ V _{CC}	V
Operating Temperature	T _{opr}	-40 ~ 85	°C
Input Rise and Fall Time	t _r , t _f	0 ~ 500 (V _{CC} =4.5V)	ns

INPUT and OUTPUT
EQUIVALENT CIRCUIT



DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	V _{CC}	T _a =25°C			T _a =-40~85°C		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
High-Level Input Voltage	V _{IH}		4.5 ≥ 5.5	2.0	-	-	2.0	-	V
Low-Level Input Voltage	V _{IL}		4.5 ≥ 5.5	-	-	0.8	-	0.8	
High-Level Output Voltage	V _{OH}	V _{IN} =V _{IH} or V _{IL}	I _{OH} =-20μA	4.5	4.4	4.5	-	4.4	-
			I _{OH} =-6mA	4.5	4.18	4.31	-	4.13	-
Low-Level Output Voltage	V _{OL}	V _{IN} =V _{IH} or V _{IL}	I _{OL} =20μA	4.5	-	0.0	0.1	-	0.1
			I _{OL} =6mA	4.5	-	0.17	0.26	-	0.33
3-State Output Off-State Current	I _{OZ}	V _{IN} =V _{IH} or V _{IL} V _{OUT} =V _{CC} or GND	5.5	-	-	±0.5	-	±5.0	μA
Input Leakage Current	I _{IN}	V _{IN} =V _{CC} or GND	5.5	-	-	±0.1	-	±1.0	
Quiescent Supply Current	I _{CC}	V _{IN} =V _{CC} or GND	5.5	-	-	4.0	-	40.0	
Supply Current	I _C	Per input: V _{IN} =2.4V or 0.5V Other input: V _{CC} or GND	5.5	-	-	2.0	-	2.9	mA

TC74HCT563P

TC74HCT573P

AC ELECTRICAL CHARACTERISTICS (C_L=50pF, Input t_r=t_f=6ns)

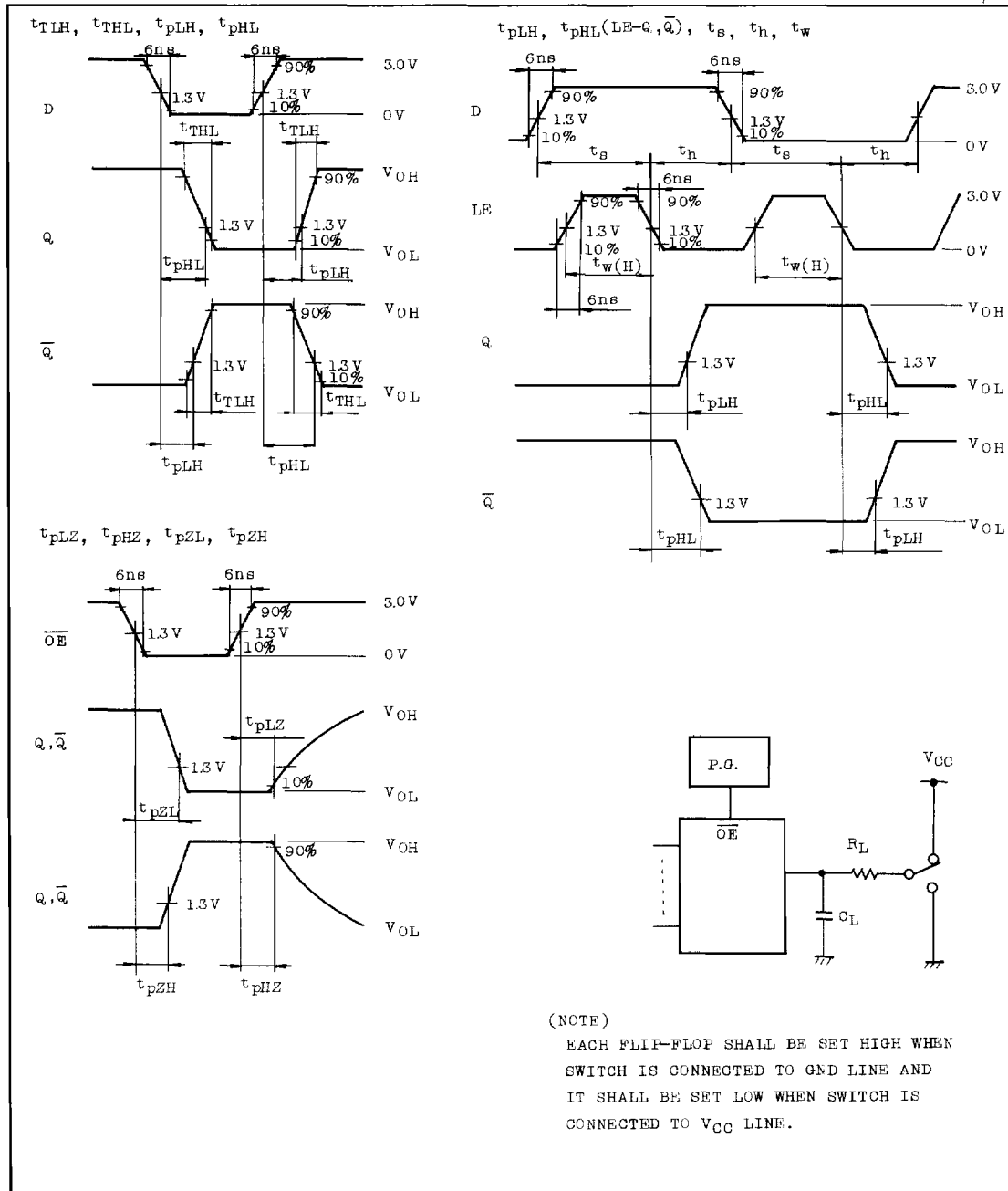
PARAMETER	SYMBOL	TEST CONDITION	V _{CC}	Ta=25°C			Ta=-40~85°C		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
Output Transition Time	t _{TLH}		4.5	-	7	12	-	19	ns
	t _{THL}								
Propagation Delay Time (LE - Q, \bar{Q})	t _{pLH}		4.5	-	24	35	-	44	
	t _{pHL}								
Propagation Delay Time (D - Q, \bar{Q})	t _{pLH}		4.5	-	22	35	-	44	
	t _{pHL}								
Minimum Pulse Width (LE)	t _{w(H)}		4.5	-	8	15	-	19	
Minimum Set-up Time	t _s		4.5	-	2	10	-	13	
Minimum Hold Time	t _h		4.5	-	-	5	-	5	
3-State Output Enable Time	t _{pZL}	R _L =1kΩ	4.5	-	18	35	-	44	
	t _{pZH}								
3-State Output Disable Time	t _{pLZ}	R _L =1kΩ	4.5	-	26	37	-	46	
	t _{pHZ}								
Input Capacitance	C _{IN}			-	5	10	-	10	pF
Output Capacitance	C _{OUT}			-	10	-	-	-	
Power Dissipation Capacitance	C _{PD(1)}	TC74HCT563		-	41	-	-	-	
		TC74HCT573		-	41	-	-	-	

Note (1): C_{PD} is defined as the value of internal equivalent capacitance of IC which is calculated from the operating current consumption without load (refer to Test Circuit).

Average operating current can be obtained by the equation hereunder.

$$I_{CC(opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 \quad (\text{per Latch})$$

SWITCHING CHARACTERISTICS TEST WAVEFORM



TC74HCT563P TC74HCT573P

$I_{CC(Oper.)}$ TEST CIRCUIT

